

Form PTO-1449
(Rev. 8-83)Department of Commerce
Patent and Trademark Office

Atty Docket 01/27

Serial No. 09/466,828

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: December 20, 1999

Group/Art Unit: 2818

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
MS	5,429,995	07/04/1995	Nishiyama et al.	437	238	7-16-93
MS	5,641,581	06/24/1997	Nishiyama et al.	428	688	3-28-98

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
MS	01-268064	10/25/1989	JP			Full Eng
MS	07-074245	03/17/1995	JP			Eng Abst

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner Initial	
MS	Van der Meulen et al., "Effects of HC1 and C1 ₂ Additions on Silicon Oxidation Kinetics", pp. 371-389, 1974, Journal of Electronic Materials. Vol. 3, No. 2
MS	Wright et al., "The Effect of Fluorine in Silicon Dioxide Gate Dielectrics", pp. 879-889, May 1989, IEEE Transactions on Electron Devices, vol. 36, No. 5
MS	Nishioka et al., "Radiation Hardened Micron and Submicron Mosfets Containing Fluorinated Oxides", pp. 2116-2123, December 1989, IEEE Transactions on Nuclear Science Vol. 36, No. 6
MS	Wright et al., "Hot-Electron Immunity of SiO ₂ Dielectrics with Fluorine Incorporation", pp. 347-348, August 1989, IEEE Electron Device Letters, Vol. 10, No. 8
MS	Baker et al., "The Influence of Fluorine on Threshold Voltage Instabilities in P+ Polysilicon Gated P-Channel Mosfets", pp. 443-446, 1989, IEDM 17.1.1
MS	MacWilliams et al., "Improved Hot-Carrier Resistance with Fluorinated Gate Oxides", pp. 3-5, January 1990, IEEE Electron Device Letters, Vol. 11, No. 1

Examiner

Date Considered 1/14/01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

09/05/2001